



Title of Change:	Power phase Trench 6 Technology Capacity Expansion by Qualification of Aizu Fujitsu Semiconductor Manufacturing, Japan		
Proposed first ship date:	20 March 2017		
Contact information:	Contact your local ON Semiconductor Sales Office or <Aditya.Jain@onsemi.com>		
Samples:	Contact your local ON Semiconductor Sales Office or <Aditya.Jain@onsemi.com>		
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or <Don.Knudsen@onsemi.com>		
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <PCN.Support@onsemi.com>.		
Change Part Identification:	Affected parts will be identified with a date code of WW12'17		
Change category:	☒ Wafer Fab Change ☐ Assembly Change ☐ Test Change ☐ Other _____		
Change Sub-Category(s):	☒ Manufacturing Site Change/Addition ☐ Manufacturing Process Change ☐ Material Change ☐ Product specific change ☐ Datasheet/Product Doc change ☐ Shipping/Packaging/Marking ☐ Other: _____		
Sites Affected:	☐ All site(s) ☐ not applicable ☐ ON Semiconductor site(s) : ☒ External Foundry/Subcon site(s) Aizu Fujitsu Semiconductor Manufacturing, Japan		
Description and Purpose:			
This is a final change notification to customers on the qualification of additional wafer fabrication capacity for Power Phase 30V Trench (T6) MOSFET technology in Aizu Fujitsu Semiconductor Manufacturing (AFSM) located in Aizu, Japan. At the expiration of this notification, all products listed here will be dual sourced from its current ON Semiconductor wafer fab in Gresham and AFSM.			

**Reliability Data Summary:**

QV DEVICE NAME: NTMFS4C85NT1G (HSFET)

Package: Power Phase

Test	Specification	Condition	Interval	Sample Size	Results
HTSL	JESD22-A103	Ta=150°C	2016 hrs	84pc/3 lots	0/252
IOL	MIL-STD-750	Ta=+25°C, delta Tj=100°C	15000 cyc	84pc/3 lots	0/252
	(M1037)	On/off = 2 min			
	AEC-Q101				
TC	JESD22-A104	Ta=-55°C to +150°C	2000 cyc	84pc/3 lots	0/252
H3TRB	JESD22-XXX	85°C, 85% RH, bias	2016 hrs	84pc/3 lots	0/252
uHAST	JESD22-A118	131°C, 85% RH, 18.8psig, unbiased	96 hrs	84pc/3 lots	0/252

QV DEVICE NAME:NTMFS4C85NT1G (LSFET)

Package: Power Phase

Test	Specification	Condition	Interval	Sample Size	Results
HTRB	JESD22-A108	Ta=150°C, 80% max rated Vdss	1008 hrs	84pc/3 lots	0/252
HTGB	JESD22-A108	Ta=150°C, 100% max rated Vgss	1008 hrs	84pc/3 lots	0/252
IOL	MIL-STD-750	Ta=+25°C, delta Tj=100°C	15000 cyc	84pc/3 lots	0/252
	(M1037)	On/off = 2 min			
	AEC-Q101				
TC	JESD22-A104	Ta=-55°C to +150°C	1000 cyc	84pc/3 lots	0/252
H3TRB	JESD22-XXX	85°C, 85% RH, bias	1008 hrs	84pc/3 lots	0/252
uHAST	JESD22-A118	131°C, 85% RH, 18.8psig, unbiased	96 hrs	84pc/3 lots	0/252

Electrical Characteristic Summary:

Electrical characteristics are not impacted

List of Affected Standard Parts:

Part Number	Qualification Vehicle
NTMFD4C85NT1G	NTMFD4C85NT1G
NTMFD4C85NT3G	NTMFD4C85NT1G
NTMFD4C86NT1G	NTMFD4C85NT1G
NTMFD4C86NT3G	NTMFD4C85NT1G
NTMFD4C87NT1G	NTMFD4C85NT1G
NTMFD4C87NT3G	NTMFD4C85NT1G
NTMFD4C88NT1G	NTMFD4C85NT1G
NTMFD4C88NT3G	NTMFD4C85NT1G